#### SILICON (Si) POWER MOSFET A CEU1010L



CET MOS

# **CEU1010L**

# 100V ▲ 8.5mΩ ▲ 63A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO252 (DPAK) package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





FREE

RoHS



Parameter ( $T_c = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	100V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at T <sub>c</sub> = 25°C	I <sub>D</sub>	63A
Continuous Drain Current at T <sub>c</sub> = 100°C	I <sub>D</sub>	40A
Pulsed Drain Current Note 1	I <sub>DM</sub> Note4	252A
Maximum Power Dissipation at T <sub>c</sub> = 25°C	PD	69W
Power Dissipation Derating above 25°C	ΔΡ <sub>D</sub>	0.55W/°C
Single Pulsed Avalanche Energy Note 5	E <sub>AS</sub>	74mJ
Single Pulsed Avalanche Current Note 5	I <sub>AS</sub>	38.5A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

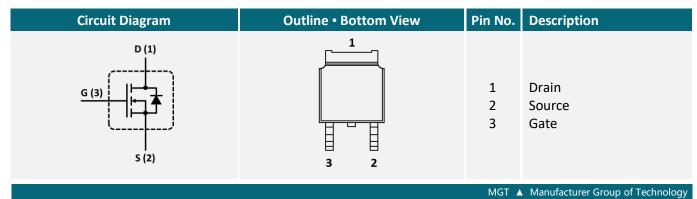
#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.8°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH_JA</sub>	50°C/W

#### **APPLICATIONS**

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

### **PIN DESCRIPTION**



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#### **ELECTRICAL CHARACTERISTICS** A T<sub>c</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 250\mu A$	BV <sub>DSS</sub>	100			V
Zero Gate Voltage Drain Current	$V_{DS}$ = 100V, $V_{GS}$ = 0V	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	V <sub>GS(th)</sub>	1		2.5	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 20A$	R <sub>DS(ON)</sub>		8.5	9.8	mΩ
Static Drain-Source On-Resistance	$V_{GS}$ = 4.5V, I <sub>D</sub> = 20A	R <sub>DS(ON)</sub>		11.4	13	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	CISS		1430		рF
Output Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	Coss		290		рF
Reverse Transfer Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		5		рF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD}$ = 50V, $V_{GS}$ = 10V, $I_D$ = 20A, $R_{G(ext)}$ = 10 $\Omega$	t <sub>D(ON)</sub>		15		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 20A, $R_{\text{G(ext)}}$ = 10 $\Omega$	t <sub>R</sub>		7		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 20A, $R_{\text{G(ext)}}$ = 10 $\Omega$	t <sub>D(OFF)</sub>		43		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 20A, $R_{\text{G(ext)}}$ = 10 $\Omega$	t <sub>F</sub>		16		ns
Total Gate Charge	$V_{DD} = 50V, V_{GS} = 4.5V, I_D = 20A$	Q <sub>G</sub>		14		nC
Gate Source Charge	$V_{DD} = 50V, V_{GS} = 4.5V, I_D = 20A$	Q <sub>GS</sub>		3		nC
Gate Drain Charge	$V_{DD}$ = 50V, $V_{GS}$ = 4.5V, $I_D$ = 20A	$\mathbf{Q}_{GD}$		8		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		I <sub>S</sub>			57	А
Drain-Source Diode Forward Voltage Note 2	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	$V_{\text{SD}}$			1.2	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

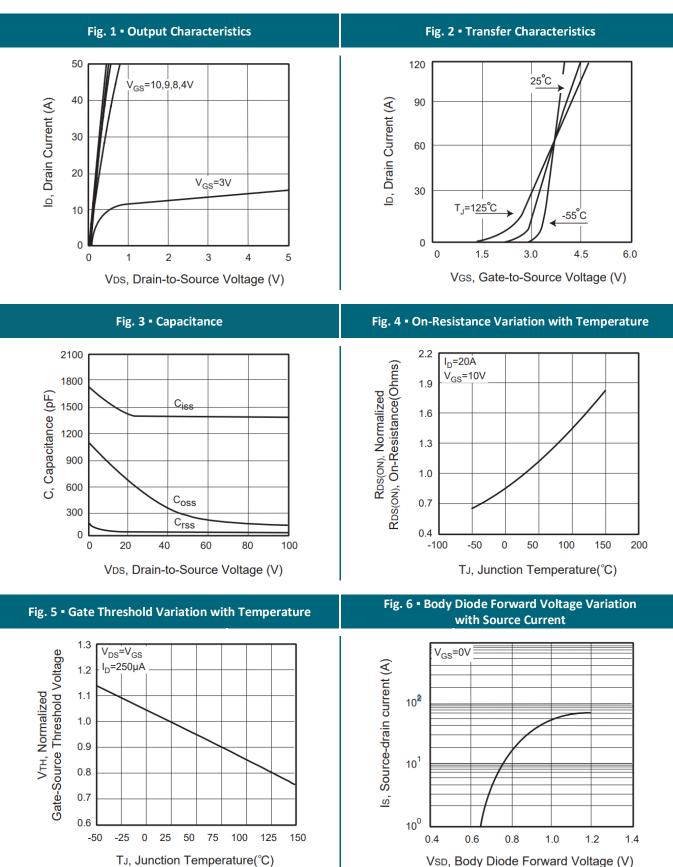
3: Guaranteed by design, not subject to production testing.

4: Pulse width limited by safe operating area.

5: L = 0.1mH,  $I_{AS}$  = 38.5A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25 $^{\circ}$ C



## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



TJ, Junction Temperature(°C)

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#### **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

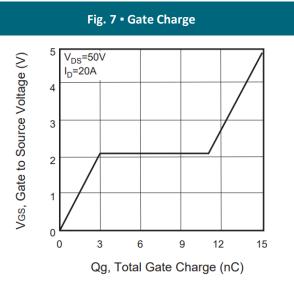


Fig. 9 - Breakdown Voltage Variation vs. Temperature

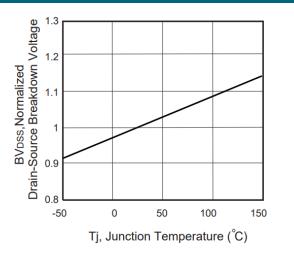
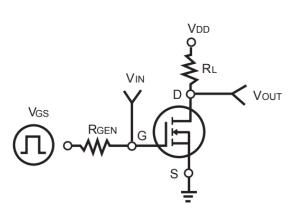


Fig. 10 - Switching Test Circuit



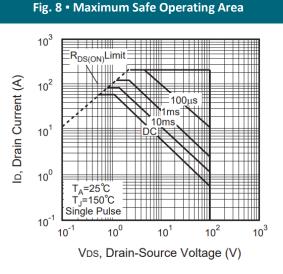
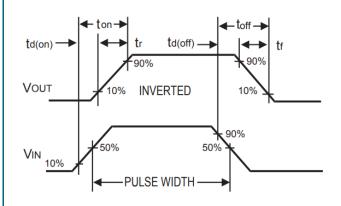


Fig. 11 • Switching Waveforms



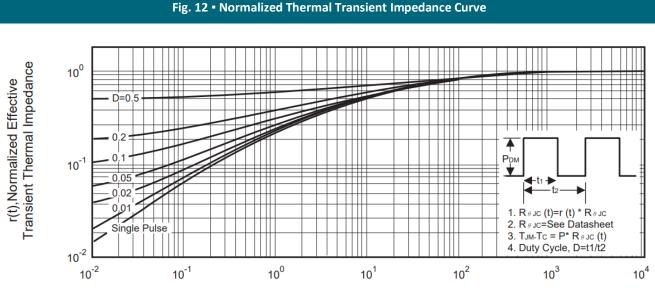
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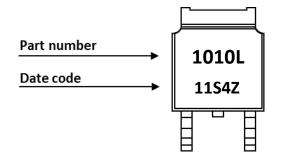


# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



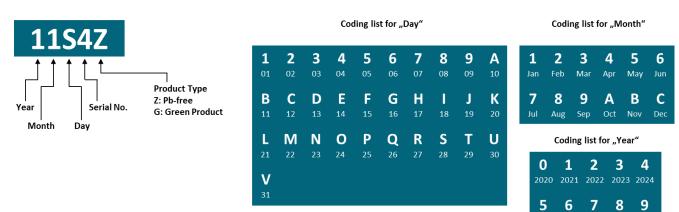
Square Wave Pulse Duration (msec)

#### PART MARKING



#### DATE CODE

Example: 11S4Z

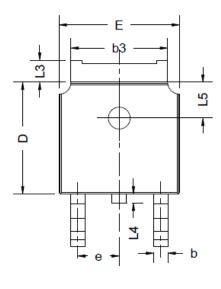


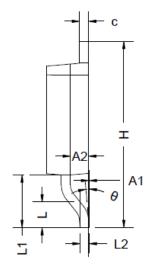
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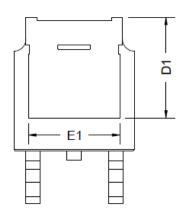
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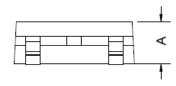


## **PACKAGE OUTLINE**









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)		Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	2.20	2.30	2.38		е		2.286 BSC	
A1	0.00	-	0.20		н	9.40	10.10	10.50
A2	0.90	1.07	1.17		L	1.38	1.50	1.75
b	0.68	0.78	0.90		L1		2.90 REF	
b3	5.23	5.33	5.46		L2		0.51 BSC	
С	0.43	0.53	0.61		L3	0.88	-	1.28
D	5.98	6.10	6.22		L4	0.50		1.00
D1		5.30 REF			L5	1.65	1.80	1.95
E	6.40	6.60	6.73		θ	0°	-	8°
E1	4.63	-	-					

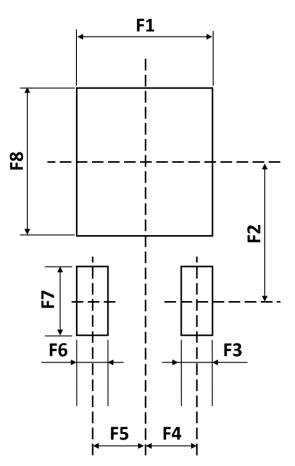
#### **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEU1010L	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs

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## **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-	F5	-	2.29	-
F2	-	6.25	-	F6	-	1.40	-
F3	-	1.40	-	F7	-	3.00	-
F4	-	2.29	-	F8	-	6.50	-

Notes:

**1**. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

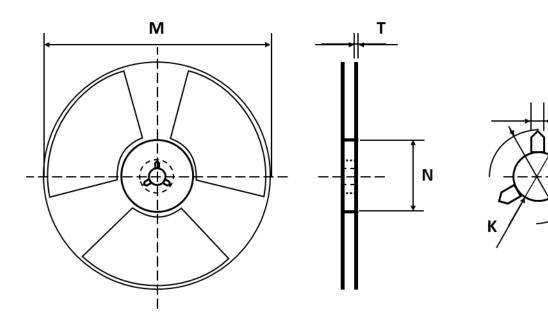


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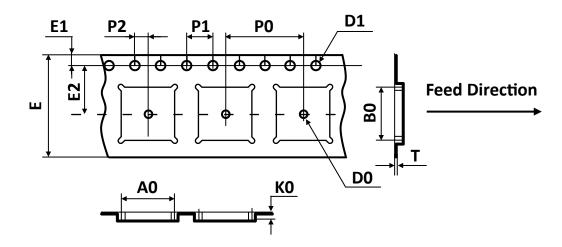


#### **REEL DIMENSIONS** All dimensions in mm



22.00		
22.00	13.00 2.0	00
±0.50		
	±0.50	±0.50 +0.50 +0. -0.20 -0.

# TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30 -0.20	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

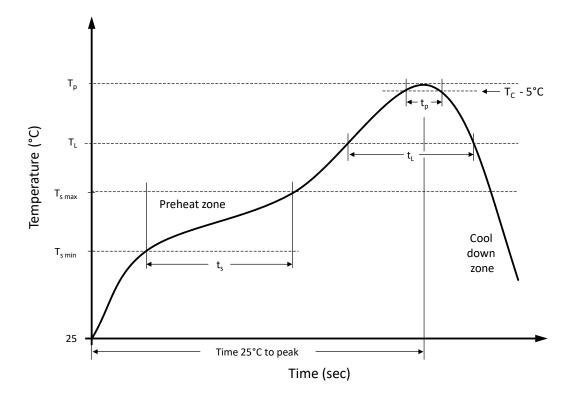


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#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



# **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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